



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts,Customers Priority,Honest Operation,and Considerate Service",our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



SICR10650CT / SICRB10650CT / SICRD10650CT / SICRF10650CT 650V SiC POWER SCHOTTKY RECTIFIER

Description


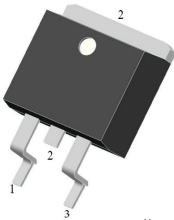


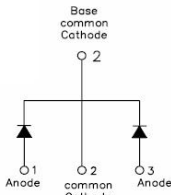
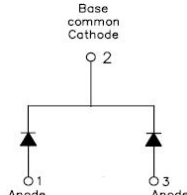
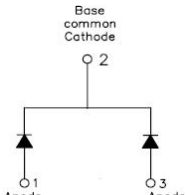
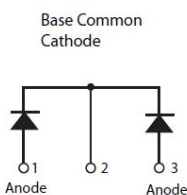
SICR10650CT/ SICRB10650CT/ SICRD10650CT/ SICRF10650CT are all common cathode SiC Schottky rectifiers packaged in TO-220AB, D2PAK, DPAK and ITO-220AB case. The device is a high voltage Schottky rectifier pair that has very low total conduction losses and very stable switching characteristics over temperature extremes. The SICR10650CT/ SICRB10650CT/ SICRD10650CT/ SICRF10650CT are ideal for energy sensitive, high frequency applications in challenging environments.

Features

- 175°C T_J operation
- Center tap configuration
- Ultra-low switching loss
- Switching speeds independent of operating temperature
- Low total conduction losses
- High forward surge current capability
- High package isolation voltage
- Guard ring for enhanced ruggedness and long term reliability
- Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional electrical and life testing can be performed upon request

Applications

- Alternative energy inverters
- Power Factor Correction (PFC)
- Free-Wheeling diodes
- Switching supply output rectification
- Reverse polarity protection

SICR10650CT	SICRB10650CT	SICRD10650CT	SICRF10650CT
			
			
TO-220AB	D ² PAK	DPAK	ITO-220AB

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	-	650	V
Average Rectified Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_c=105^\circ\text{C}$, rectangular wave form	5(Per Leg) 10(Per Device)	A
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I_{FSM}	8.3ms, Half Sine pulse	60	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop(Per Leg)*	V_{F1}	@ 5A, Pulse, $T_J = 25^\circ\text{C}$	1.5	1.7	V
	V_{F2}	@ 5A, Pulse, $T_J = 150^\circ\text{C}$	1.98	2.5	V
Reverse Current at DC condition (Per Leg)*	I_{R1}	@ $V_R = \text{rated } V_R$ $T_J = 25^\circ\text{C}$	5	60	μA
Reverse Current (Per Leg)*	I_{R2}	@ $V_R = \text{rated } V_R$ $T_J = 125^\circ\text{C}$	70	250	μA
Junction Capacitance (Per Leg)	C_T	@ $V_R = 5\text{V}$, $T_C = 25^\circ\text{C}$ $f_{SIG} = 1\text{MHz}$	-	TBD	pF
Series Inductance (Per Leg)	L_S	Measured lead to lead 5 mm from package body	-	TBD	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/ μs
RSM Isolation Voltage (t = 1.0 second, R. H. <=30%, $T_A = 25^\circ\text{C}$)	V_{ISO}	Clip mounting, the epoxy body away from the heatsink edge by more than 0.110" along the lead direction.	-	4500	V
		Clip mounting, the epoxy body is inside the heatsink.	-	3500	
		Screw mounting, the epoxy body is inside the heatsink.	-	1500	

* Pulse width < 300 μs , duty cycle < 2%

Thermal-Mechanical Specifications:

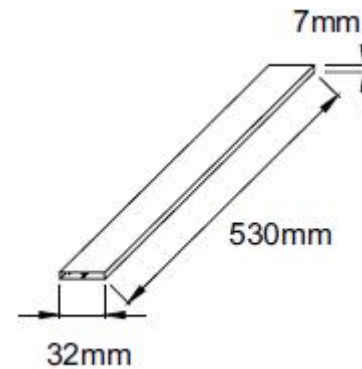
Characteristics	Symbol	SICR 10650CT	SICRB 10650CT	SICRD 10650CT	SICRF 10650CT	Units
Junction Temperature	T_J	-55 to +175				$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +175				$^\circ\text{C}$
Maximum Thermal Resistance Junction to Case	$R_{\theta JC}$	2.4	2.4	2.4	4.2	$^\circ\text{C/W}$

Ordering Information

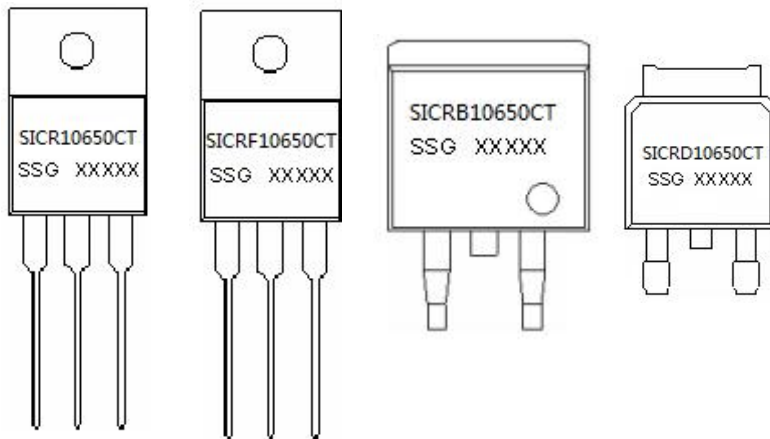
Device	Package	Weight	Shipping
SICR10650CT	TO-220AB	1.8g	50pcs / tube
SICRB10650CT	D ² PAK	1.85g	800pcs / reel
SICRD10650CT	DPAK	0.39g	2500pcs / reel
SICRF10650CT	ITO-220AB	1.8g	50pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Tube Specification(TO-220AB/ITO-220AB)



Marking Diagram

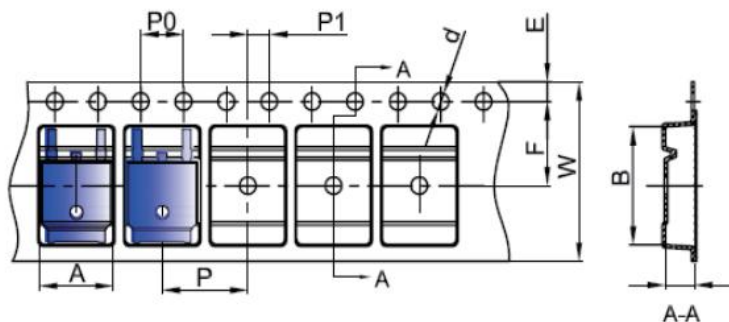


Where XXXXX is YYWWL

SICR = Device Type
B/D/F = Package type
10 = Forward Current (10A)
650 = Reverse Voltage (650V)
CT = Configuration
SSG = SSG
YY = Year
WW = Week
L = Lot Number

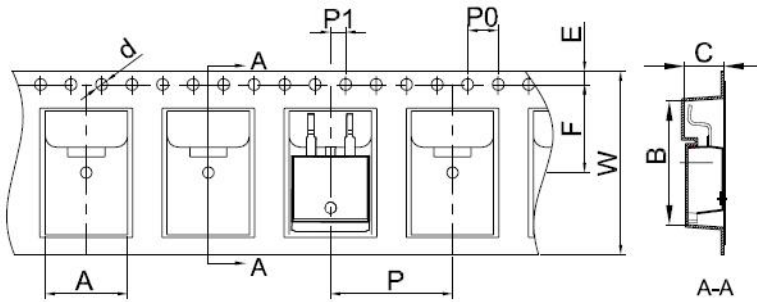
Cautions: Molding resin
Epoxy resin UL:94V-0

Carrier Tape Specification DPAK



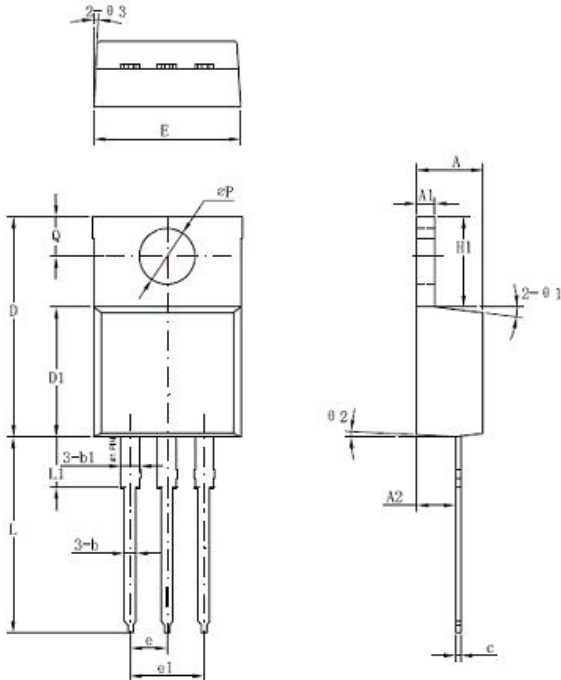
SYMBOL	Millimeters	
	Min.	Max.
A	6.80	7.00
B	10.40	10.60
C	2.60	2.80
d	Φ1.45	Φ1.65
E	1.65	1.85
F	7.40	7.60
P0	3.90	4.10
P	7.90	8.10
P1	1.90	2.10
W	15.90	16.30

Carrier Tape Specification D2PAK



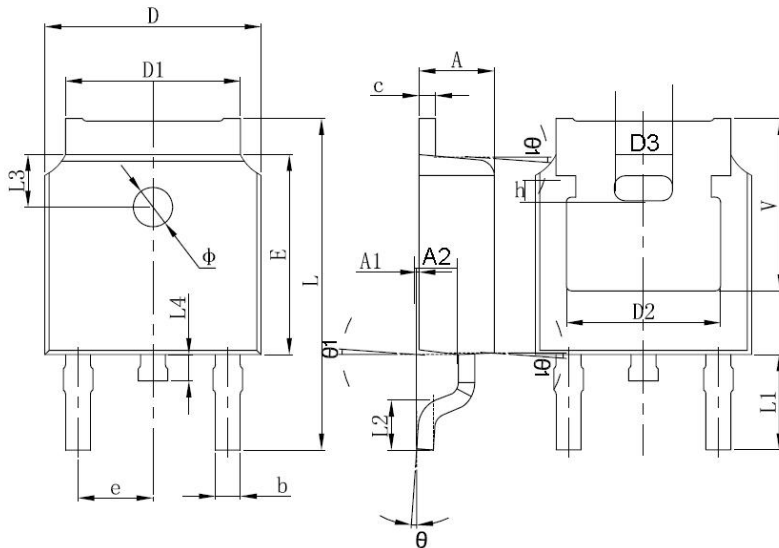
SYMBOL	Millimeters	
	Min.	Max.
A	10.70	10.90
B	16.03	16.23
C	5.11	5.31
d	1.45	1.65
E	1.65	1.85
F	11.40	11.60
P0	3.90	4.10
P	15.90	16.10
P1	1.90	2.10
W	23.90	24.30

Mechanical Dimensions TO-220AB



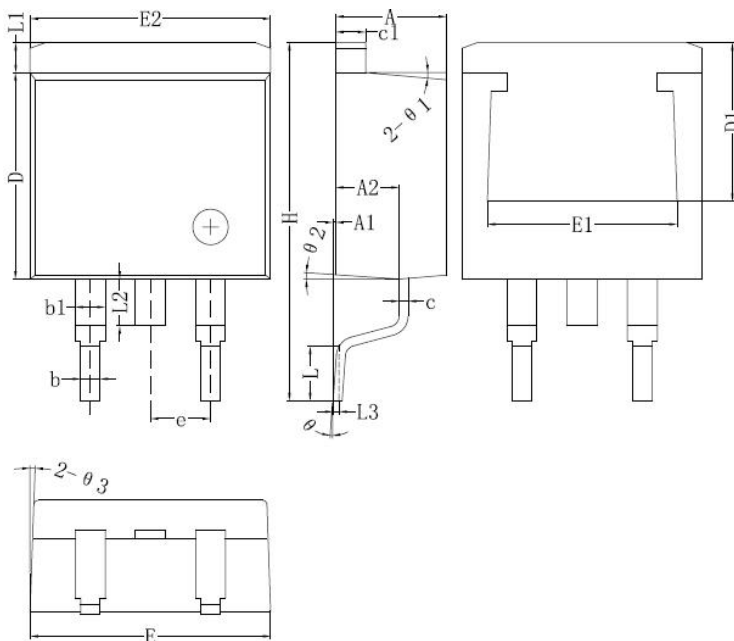
Symbol	Dimensions in millimeters		
	Min	Typical	Max
A	4.42	4.57	4.72
A1	1.17	1.27	1.37
A2	2.52	2.69	2.89
b	0.71	0.81	0.96
b1	1.17	1.27	1.37
c	0.31	0.38	0.61
D	14.94	15.24	15.54
D1	8.85	9.00	9.15
E	10.01	10.16	10.31
e		2.54	
e1	4.98	5.06	5.18
H1	6.04	6.24	6.44
L	12.7	13.56	13.80
L1	3.56	3.5	3.96
ΦP	3.74	3.84	4.04
Q	2.54	2.74	2.94
Q1		7°	
Q2		3°	
Q3		4°	

Mechanical Dimensions DPAK



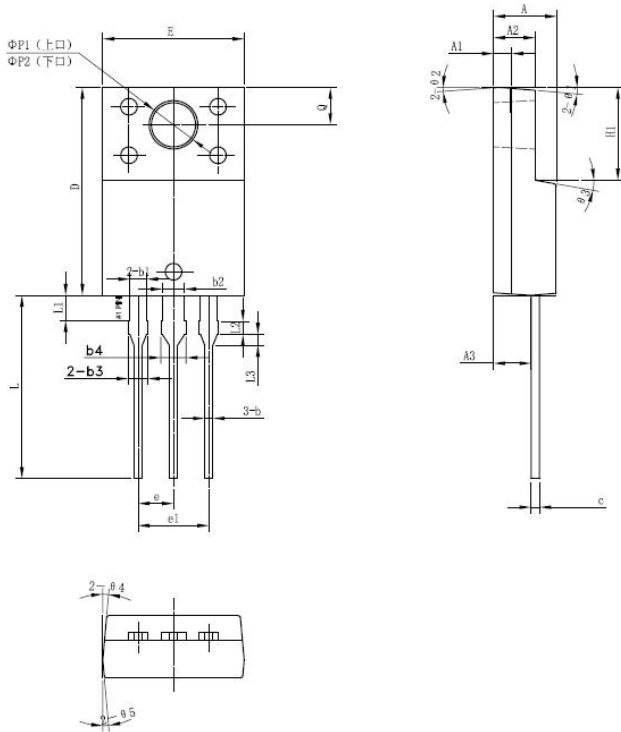
SYMBOL	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	2.20	2.40	0.087	0.094
A1	0.00	0.127	0.000	0.005
b	0.66	0.86	0.026	0.034
c	0.46	0.60	0.018	0.024
D	6.50	6.70	0.256	0.264
D1	5.13	5.46	0.202	0.215
D2	4.83 REF.		0.190 REF.	
E	6.00	6.20	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.70	10.40	0.381	0.409
L1	2.90 REF.		0.144 REF.	
L2	1.40	1.70	0.055	0.067
L3	1.60 REF.		0.063 REF.	
L4	0.60	1.00	0.024	0.039
Φ	1.10	1.30	0.043	0.051
Θ	0°	8°	0°	8°
h	0.00	0.30	0.000	0.012
V	5.35 REF.		0.211 REF.	

Mechanical Dimensions D²PAK



Symbol	Dimensions in millimeters		
	Min.	Typical	Max.
A	4.55	4.70	4.85
A1	0	0.10	0.25
A2	2.59	2.69	2.89
b	0.71	0.81	0.96
b1		1.27	
c	0.36	0.38	0.61
c1	1.17	1.27	1.37
D	8.55	8.70	8.85
D1	6.40		
E	10.01	10.16	10.31
E1	7.6		
E2	9.98	10.08	10.18
e		2.54	
H	14.6	15.1	15.6
L	2.00	2.30	2.70
L1	1.17	1.27	1.40
L2			2.20
L3		0.25BSC	
e	0	-	8°
e1		5°	
e2		4°	
e3		4°	

Mechanical Dimensions ITO-220AB



SYMBOL	Millimeters		
	MIN.	TYP.	MAX.
A	4.30	4.50	4.70
A1	1.10	1.30	1.50
A2	2.50	3.00	3.20
A3	2.50	2.70	2.90
b	0.50	0.60	0.75
b1	1.10	1.20	1.35
b2	1.50	1.60	1.75
b3	1.20	1.30	1.45
b4	1.60	1.70	1.85
c	0.50	0.60	0.75
D	14.80	15.00	15.20
E	9.96	10.16	10.36
e		2.55	
e1		5.10	
H1	6.50	6.70	6.90
L	12.70	13.20	13.70
L1	1.60	1.80	2.00
L2	0.80	1.00	1.20
L3	0.60	0.80	1.00
$\Phi P1$ (上口)	3.30	3.50	3.70
$\Phi P2$ (下口)	2.99	3.19	3.39
Q	2.50	2.70	2.90
$\Theta 1$		5°	
$\Theta 2$		4°	
$\Theta 3$		10°	
$\Theta 4$		5°	
$\Theta 5$		5°	

Technical Data
Data Sheet N1871, Draft 1



DISCLAIMER:

- 1- The information given herein, including the specifications and dimensions, is subject to change without prior notice to improve product characteristics. Before ordering, purchasers are advised to contact the SMC - Sangdest Microelectronics (Nanjing) Co., Ltd sales department for the latest version of the datasheet(s).
- 2- In cases where extremely high reliability is required (such as use in nuclear power control, aerospace and aviation, traffic equipment, medical equipment, and safety equipment), safety should be ensured by using semiconductor devices that feature assured safety or by means of users' fail-safe precautions or other arrangement.
- 3- In no event shall SMC - Sangdest Microelectronics (Nanjing) Co., Ltd be liable for any damages that may result from an accident or any other cause during operation of the user's units according to the datasheet(s). SMC - Sangdest Microelectronics (Nanjing) Co., Ltd assumes no responsibility for any intellectual property claims or any other problems that may result from applications of information, products or circuits described in the datasheets.
- 4- In no event shall SMC - Sangdest Microelectronics (Nanjing) Co., Ltd be liable for any failure in a semiconductor device or any secondary damage resulting from use at a value exceeding the absolute maximum rating.
- 5- No license is granted by the datasheet(s) under any patents or other rights of any third party or SMC - Sangdest Microelectronics (Nanjing) Co., Ltd.
- 6- The datasheet(s) may not be reproduced or duplicated, in any form, in whole or part, without the expressed written permission of SMC - Sangdest Microelectronics (Nanjing) Co., Ltd.
- 7- The products (technologies) described in the datasheet(s) are not to be provided to any party whose purpose in their application will hinder maintenance of international peace and safety nor are they to be applied to that purpose by their direct purchasers or any third party. When exporting these products (technologies), the necessary procedures are to be taken in accordance with related laws and regulations..